

Φ5 PIN SILICON PHOTO TRANSISTOR LED LAMPS

PART NO: NFL-5123PTC

REV NO: 1.0

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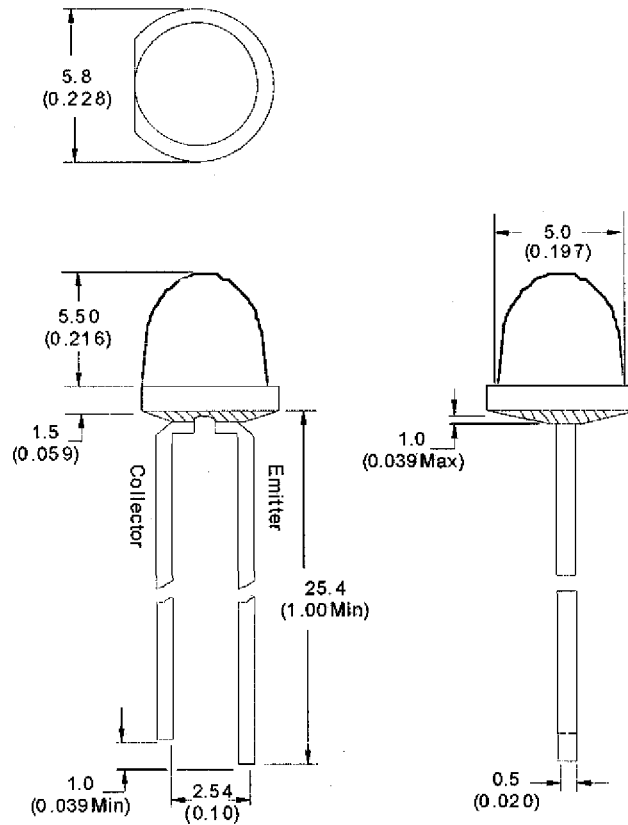
- Features:

- High illumination sensitivity.
- Stable characteristics.

- Descriptions:

- The NFL-5123PTC is a silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of NFL-5123PTC is encapsulated in clear plastic T1 3/4 package individually.

- Package Dimensions:



NOTES:

1. All dimension are in millimeters(inch).
2. An epoxy meniscus may extend about 1.0mm down to the lead.
3. Tolerances unless dimension • ± 0.25 mm.

DATE:2004/08/12

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• Absolute Maximum Ratings at Ta=25

Parameter	Symbol	Rating	Unit
Power Dissipation	P_d	100	mW
Collector-Emitter Breakdown Voltage	BV_{CEO}	30	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	5	V
Operation Temperature	T_{OPR}	-40 to +80	• •
Storage Temperature	T_{STG}	-40 to +85	• •
Lead Soldering Temperature	T_{SOL}	Max.260 • 5 • for 3 sec Max. (1.6mm from the base of the epoxy bulb)	• •

• Electronic Optical Characteristics at Ta=25

Items	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-Emitter Breakdown Voltage	BV_{CEO}	30	-	-	V	• $I_{EO}=100\mu A$
Emitter-Collector Breakdown Voltage	BV_{ECO}	5	-	-	V	• $I_{CO}=100\mu A$
Collector-Base Breakdown Voltage	BV_{CBO}	40	-	-	V	• $I_{BO}=100\mu A$
Collect-Emitter Saturation Voltage	$V_{CE(SAT)}$	-	0.2	0.4	V	• $I_B=1mA$ • $I_C=2mA$
Dark Current	I_{CEO}	-	-	100	nA	• $I_E=20V$
Rise/Fall Time	T_r/T_f	-	5/5	-	μS	$R_L=1000 \cdot \cdot$ $V_{CE}=10V$
On State Collector Current	I_P	1		2	mA	• $I_E=5V$ $H=1mW/cm^2$ $\lambda=940nm$
		2		4	mA	
		4		8	mA	
		8			mA	